

Micromechanical electrometry of single-electron transistor island charge

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Abstract

We consider the possibility of using a micromechanical gate electrode located just above the island of a single-electron transistor to measure directly the fluctuating island charge due to tunnelling electrons.

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Single-electron transistors (SETs) [1] have proven to be exquisitely sensitive electrometers, with the best reported lower noise values of about $10^{-5} e/\sqrt{\text{Hz}}$ [2,3]. Further improvements in sensitivity require an understanding of the origins of the background charge fluctuations (see, e.g., Ref. [2], and references therein) which dominate over the intrinsic tunnelling shot noise of current devices. By contrast, there has been little work on probing directly the intrinsic noise of the SET itself. In a relevant investigation [4], a superconducting SET was coupled capacitively to a SET island in order to measure the charge

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state of the island. Such investigations provide additional valuable tests of our understanding of the SET dynamics, as represented by the orthodox theory [5].

In the present work we consider the possibility of using micromechanical electrometry to measure directly the fluctuating SET island charge due to electrons tunnelling onto and off the island [6]. A cantilever gate electrode located directly above the SET island with displacement measured using either the magnetomotive method [11] or fibre optic interferometer [10] might serve as the electrometer.

We first derive an order of magnitude estimate of the spectral density of the force acting on the cantilever due to the fluctuating island charge. In terms of the SET source-drain voltage V_{sd} , the gate voltage V_g and the number n of excess electrons on the SET island, the electrostatic energy stored in the gate capacitor C_g is

$$U = \frac{C_g}{2C_\Sigma^2} [C(V_{sd} - 2V_g) - ne]^2,$$

where we assume a symmetric SET with tunnel junction capacitances $C_1 = C_2 = C$, effective resistances $R_1 = R_2 = R$, total capacitance $C_\Sigma = 2C + C_g$ and we have neglected a possible background island charge since it will not affect the final result. For small displacements of the cantilever gate electrode, $C_g \approx C_g^0(1 - x/d)$, where d is the cantilever electrode-SET island gap, and the force on the cantilever is

$$F = -\frac{\partial U}{\partial x} = \frac{1}{d} \left(\frac{2C - C_g}{2C + C_g} \right) U,$$

where we have dropped the superscript ‘0’ on C_g . At a given source-drain

current peak maximum, n , V_g and V_{sd} satisfy the condition

$$e(n + 1/2) = C_g(V_g - V_{sd}/2)$$

and the probabilities at any given time that there are either n or $n+1$ electrons on the island are approximately equal to $1/2$, provided the current peaks are well-separated in gate voltage. The force noise is also a maximum at a current peak maximum; we will restrict ourselves to evaluating this force noise maximum which takes a particularly simple form. An estimate for the force noise is $S_F = [F(n+1) - F(n)]^2 / (I_{sd}/e)$, where $I_{sd} = V_{sd}/4R$ is the peak maximum source-drain current. Substituting V_g and V_{sd} for n using the above condition we obtain

$$S_F = \frac{4e^3 R}{V_{sd}} \left[\frac{C_g(2C - C_g)(V_g - V_{sd}/2)}{dC_\Sigma^2} \right]^2.$$

A full derivation of $S_F(\omega)$ using the orthodox theory along the lines of Ref. [7] yields the same result at $\omega = 0$ and at a current peak maximum, differing only by an overall factor of $1/4$ [8].

The minimum detectable force is set by the intrinsic thermomechanical noise of the cantilever. For a cantilever with geometry $l \times w \times t$ (length $\times$ width $\times$ thickness), quality factor Q , Young's modulus E and mass density ρ , the thermomechanical force noise is

$$S_F^{\text{th}}^{1/2} = \left(\frac{wt^2}{lQ} \right)^{1/2} (E\rho)^{1/4} (k_B T)^{1/2}.$$

Provided there are no constraints on frequency, sensitive force detection therefore requires long and thin cantilevers with large quality factors [9]. The current best sensitivity is about 0.8 aN in a 1 Hz bandwidth [10]. For the readily

achievable values $R = 50 \text{ k}\Omega$, $C = 0.25 \text{ fF}$, $C_g = 0.1 \text{ fF}$ (corresponding to a $1 \text{ }\mu\text{m}^2$ plate area and $0.1 \text{ }\mu\text{m}$ plate gap d) and $V_{\text{sd}} = 0.1 \text{ mV}$ ($= 0.4e/C_\Sigma$), the SET force noise is

$$S_F^{1/2} \approx 1.5V_g \text{ aN}/\sqrt{\text{Hz}}$$

for $V_g \gg V_{\text{sd}}$. Thus the SET force noise would be detectable for $V_g \sim 1 \text{ V}$. However, for such voltages, pull-in of the cantilever to the substrate surface would likely occur. A possible way to avoid this problem is to orient the cantilever perpendicular to the surface [9].

Another possible approach is to use a shorter, stiffer cantilever and apply a gate voltage $V_g = V_g^0 + V_{\text{ac}} \cos(2\pi\nu t)$, with $V_g^0 \sim 1 \text{ V}$ chosen such that I_{sd} is at a given peak maximum, $V_{\text{ac}} = e/2C_g = 0.8 \text{ mV}$, and the frequency ν chosen to be smaller than the cantilever damping rate. By measuring both the amplitude and phase of the cantilever displacement and averaging over sufficiently many cycles [11], the dependence of the SET force noise on gate voltage for a given current peak can be determined.

Further work needs to be done to determine the response of the cantilever electrode to the fluctuating SET island charge. In particular, the backaction of the cantilever on the SET must also be taken into account which requires solving for the dynamics of coupled SET-cantilever system. This will be the subject of a future work.

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